DATA SHEET



MOS FIELD EFFECT TRANSISTOR

NP84N075EUE, NP84N075KUE

NP84N075CUE, NP84N075DUE, NP84N075MUE, NP84N075NUE

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

These products are N-channel MOS Field Effect Transistors designed for high current switching applications.

ORDERING INFORMATION

PART NUMBER	LEAD PLATING	PACKING	PACKAGE	
NP84N075EUE-E1-AY Note1, 2			TO 000 (MD 057 IV	
NP84N075EUE-E2-AY Note1, 2	Davis Co. (Tip.)	T 000/	TO-263 (MP-25ZJ) typ. 1.4 g	
NP84N075KUE-E1-AY Note1	Pure Sn (Tin)	Tape 800 p/reel	TO 000 (MD 057(0))	
NP84N075KUE-E2-AY Note1			TO-263 (MP-25ZK) typ. 1.5 g	
NP84N075CUE-S12-AZ Note1, 2	Sn-Ag-Cu		TO-220 (MP-25) typ. 1.9 g	
NP84N075DUE-S12-AY Note1, 2		Tube 50 p/tube	TO-262 (MP-25 Fin Cut) typ. 1.8 g	
NP84N075MUE-S18-AY Note1	Pure Sn (Tin)		TO-220 (MP-25K) typ. 1.9 g	
NP84N075NUE-S18-AY Note1			TO-262 (MP-25SK) typ. 1.8 g	

Notes 1. Pb-free (This product does not contain Pb in the external electrode.)

2. Not for new design

FEATURES

- Channel temperature 175 degree rated
- Super low on-state resistance

 $R_{DS(on)}$ = 12.5 m Ω MAX. (Vgs = 10 V, ID = 42 A)

• Low input capacitance

Ciss = 5600 pF TYP.

(TO-220)



(TO-262)





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Not all products and/or types are available in every country. Please check with an NEC Electronics

sales representative for availability and additional information.

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (Vgs = 0 V)	VDSS	75	V
Gate to Source Voltage (VDS = 0 V)	Vgss	±20	V
Drain Current (DC) (Tc = 25°C) Note1	I _{D(DC)}	±84	Α
Drain Current (pulse) Note2	ID(pulse)	±260	Α
Total Power Dissipation (T _A = 25°C)	P _{T1}	1.8	W
Total Power Dissipation (Tc = 25°C)	P _{T2}	200	W
Channel Temperature	Tch	175	°C
Storage Temperature	Tstg	-55 to +175	°C
Single Avalanche Current Note3	las	19/52/73	Α
Single Avalanche Energy Note3	Eas	333/250/50	mJ

Notes 1. Calculated constant current according to MAX. allowable channel temperature.

- **2.** PW \leq 10 μ s, Duty cycle \leq 1%
- 3. Starting T_{ch} = 25°C, V_{DD} = 35 V, R_G = 25 Ω , V_{GS} = 20 \rightarrow 0 V (See Figure 4.)

THERMAL RESISTANCE

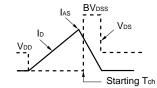
Channel to Case Thermal Resistance	Rth(ch-C)	0.75	°C/W
Channel to Ambient Thermal Resistance	Rth(ch-A)	83.3	°C/W

ELECTRICAL CHARACTERISTICS (TA = 25°C)

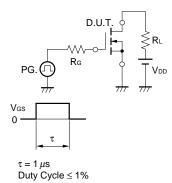
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 75 V, V _{GS} = 0 V			10	μА
Gate Leakage Current	Igss	V _{GS} = ±20 V, V _{DS} = 0 V			±100	nA
Gate to Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2.0	3.0	4.0	V
Forward Transfer Admittance	yfs	V _{DS} = 10 V, I _D = 42 A	21	43		S
Drain to Source On-state Resistance	RDS(on)	V _{GS} = 10 V, I _D = 42 A		9.3	12.5	mΩ
Input Capacitance	Ciss	V _{DS} = 25 V,		5600	8400	pF
Output Capacitance	Coss	V _{GS} = 0 V,		530	800	pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		270	490	pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 38 V, I _D = 42 A,		30	66	ns
Rise Time	tr	V _{GS} = 10 V,		21	53	ns
Turn-off Delay Time	t _{d(off)}	R _G = 0 Ω		72	150	ns
Fall Time	tr			12	30	ns
Total Gate Charge	Q _G	V _{DD} = 60 V,		100	150	nC
Gate to Source Charge	Qgs	V _{GS} = 10 V,		24		nC
Gate to Drain Charge	Q _{GD}	I _D = 84 A		35		nC
Body Diode Forward Voltage	V _{F(S-D)}	I _F = 84 A, V _{GS} = 0 V		1.0		V
Reverse Recovery Time	trr	I _F = 84 A, V _{GS} = 0 V,		70		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/μs		200		nC

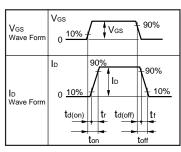
TEST CIRCUIT 1 AVALANCHE CAPABILITY

$\begin{array}{c|c} D.U.T. \\ R_G = 25 \Omega \\ \hline \\ V_{GS} = 20 \text{ V} \rightarrow 0 \text{ V} \end{array}$



TEST CIRCUIT 2 SWITCHING TIME





TEST CIRCUIT 3 GATE CHARGE

TYPICAL CHARACTERISTICS (TA = 25°C)

Figure 1. DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA

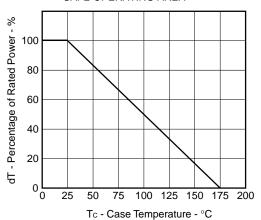


Figure 3. FORWARD BIAS SAFE OPERATING AREA

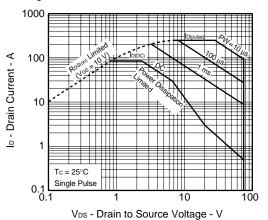


Figure 2. TOTAL POWER DISSIPATION vs. CASE TEMPERATURE

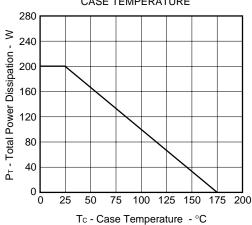


Figure 4. SINGLE AVALANCHE ENERGY DERATING FACTOR

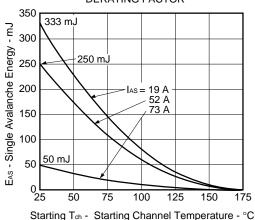


Figure 5. TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

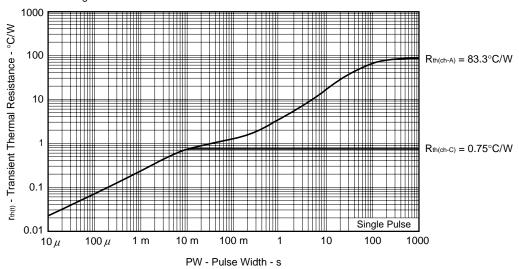


Figure 6. FORWARD TRANSFER CHARACTERISTICS

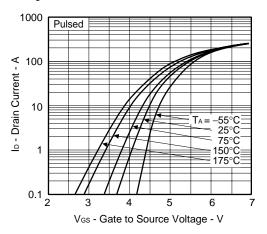
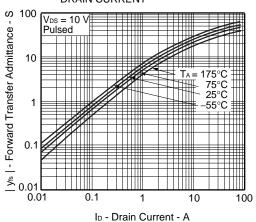


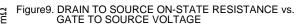
Figure7. DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE 400 Pulsed 320 Ip - Drain Current - A 240 V_{GS} = 10 V 160 80 0

2

V_{DS} - Drain to Source Voltage - V

Figure8. FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT





8

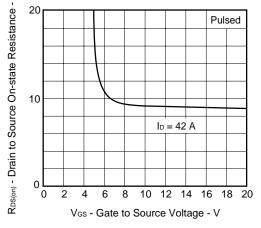


Figure 10. DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

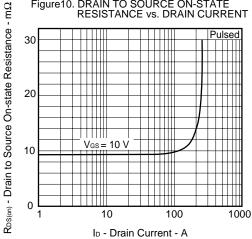
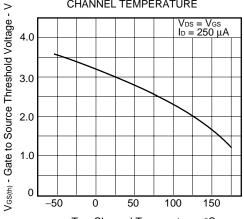


Figure11. GATE TO SOURCE THRESHOLD VOLTAGE vs. CHANNEL TEMPERATURE



Tch - Channel Temperature - °C

Figure 12. DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE

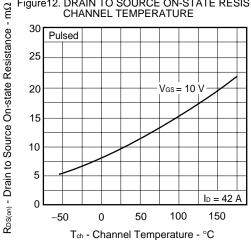


Figure 13. SOURCE TO DRAIN DIODE FORWARD VOLTAGE

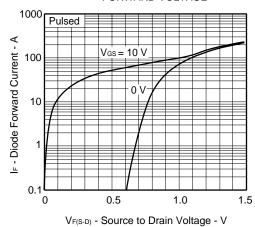


Figure 14. CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

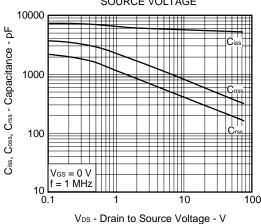


Figure 15. SWITCHING CHARACTERISTICS

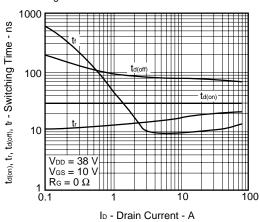


Figure16. REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT

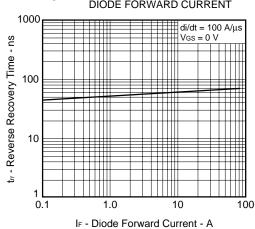
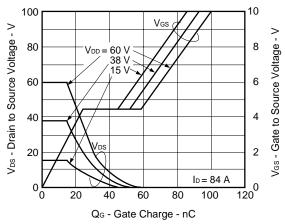
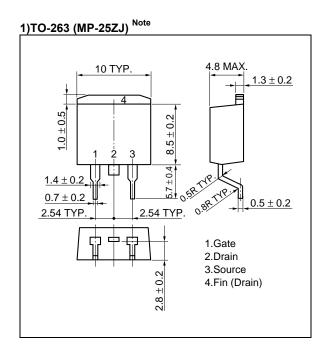
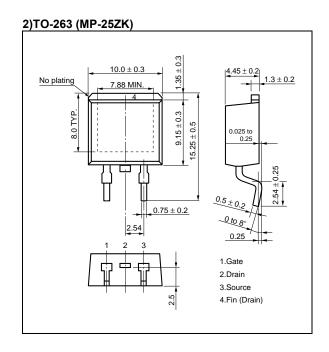


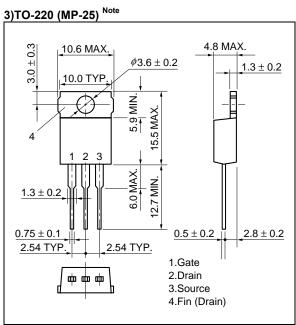
Figure 17. DYNAMIC INPUT/OUTPUT CHARACTERISTICS

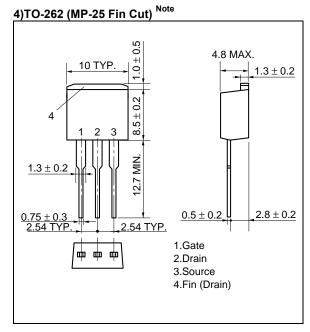


<R> PACKAGE DRAWINGS (Unit: mm)

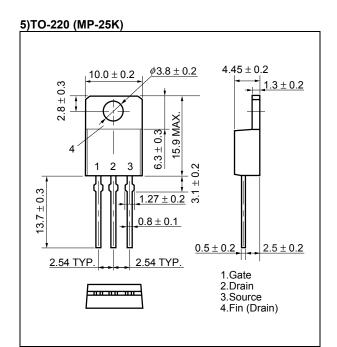


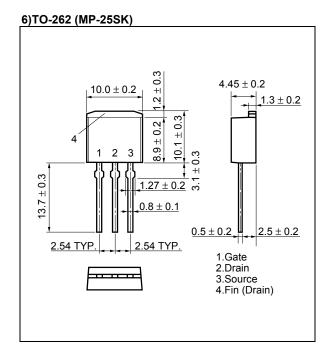




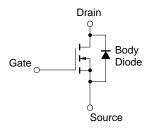


Note Not for new design





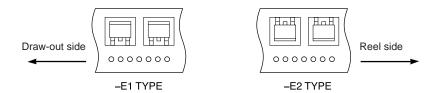
EQUIVALENT CIRCUIT



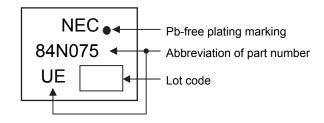
Remark Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

<R> TAPE INFORMATION

There are two types (-E1, -E2) of taping depending on the direction of the device.



<R> MARKING INFORMATION



<R> RECOMMENDED SOLDERING CONDITIONS

These products should be soldered and mounted under the following recommended conditions.

For soldering methods and conditions other than those recommended below, please contact an NEC Electronics sales representative.

For technical information, see the following website.

Semiconductor Device Mount Manual (http://www.necel.com/pkg/en/mount/index.html)

Soldering Method	Soldering Conditions	Recommended Condition Symbol	
Infrared reflow	Maximum temperature (Package's surface temperature): 260°C or below		
MP-25ZJ, MP-25ZK	Time at maximum temperature: 10 seconds or less		
	Time of temperature higher than 220°C: 60 seconds or less	ID00.00.0	
	Preheating time at 160 to 180°C: 60 to 120 seconds	IR60-00-3	
	Maximum number of reflow processes: 3 times		
	Maximum chlorine content of rosin flux (percentage mass): 0.2% or less		
Wave soldering	Maximum temperature (Solder temperature): 260°C or below		
MP-25, MP-25K, MP-25SK,	Time: 10 seconds or less	THDWS	
MP-25 Fin Cut	Maximum chlorine content of rosin flux: 0.2% (wt.) or less		
Partial heating	Maximum temperature (Pin temperature): 350°C or below		
MP-25ZJ, MP-25ZK,	Time (per side of the device): 3 seconds or less	P350	
MP-25K, MP-25SK	Maximum chlorine content of rosin flux: 0.2% (wt.) or less		
Partial heating	Maximum temperature (Pin temperature): 300°C or below		
MP-25, MP-25 Fin Cut	Time (per side of the device): 3 seconds or less	P300	
	Maximum chlorine content of rosin flux: 0.2% (wt.) or less		

Caution Do not use different soldering methods together (except for partial heating).

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